



JH3400A

N-Channel MOSFET

FEATURES

- Trench Power LV MOSFET technology
- High density cell design for low $R_{DS(on)}$
- High Speed switching



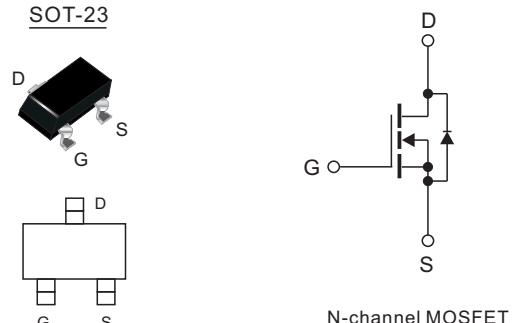
Product Summary			
V_{DS}	$R_{DS(on)}\text{ (m}\Omega\text{) Typ}$	$I_D\text{ (A)}$	$Q_g\text{ (Typ)}$
30V	21 @ 10V	5. 6	4. 8nC
	25 @ 4.5V	5. 0	

APPLICATIONS

- Battery protection
- Load switch
- Power management

MECHANICAL DATA

- Case:SOT-23(TO-236)
- Terminals:Plated solderable per MIL-STD-750,method 2026
- Mounting Position: Any



Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameters	Symbol	Value	Unit
Drain-Source voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ($T_J = 25^\circ C$ $= 150^\circ C$)	I_D	5. 6	A
		4. 5	
Pulsed Drain Current ¹⁾	I_{DM}	23	A
Maximum Power Dissipation @ $T_A=25^\circ C$	P_D	1. 2	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Thermal Resistance Ratings

Parameters	Symbol	Typ	Max	Unit
Junction to Ambient, Steady State ²⁾	R_{JA}	-	104	°C/W

RATINGS AND CHARACTERISTIC OF JH3400A

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameters	Symbol	Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	30	-	-	V
Zero Gate Voltage Drain Current	$I_{\text{DS}}^{\text{SS}}$	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}, T_c=25^\circ\text{C}$	-	-	1	μA
Gate-Source Leakage Current	$I_{\text{GS}}^{\text{SS}}$	$V_{\text{GS}}=\pm 12\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Gate-Source Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	0.65	0.9	1.5	V
Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=5.6\text{A}$	-	21	27	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=5.0\text{A}$	-	25	33	
		$V_{\text{GS}}=2.5\text{V}, I_{\text{D}}=3.0\text{A}$	-	33	51	
Dynamic						
Input Capacitance	C_{iss}	$V_{\text{DS}}=15\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	-	535	-	pF
Output Capacitance	C_{oss}		-	130	-	
Reverse Transfer Capacitance	C_{rss}		-	56	-	
Total Gate Charge	Q_g	$V_{\text{DS}}=15\text{V}, V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=5.6\text{A}$	-	4.8	-	nc
Gate-Source Charge	Q_{GS}		-	1.2	-	
Gate-Drain Charge	Q_{GD}		-	1.7	-	
Turn-on Delay Time	$t_{\text{D(on)}}$	$V_{\text{GS}}=10\text{V}, V_{\text{DD}}=30\text{V}, I_{\text{D}}=300\text{mA}, R_{\text{GEN}}=6\Omega$	-	12	-	ns
Turn-On Rise Time	t_r		-	52	-	
Turn-off Delay Time	$t_{\text{D(off)}}$		-	17	-	
Turn-Off Fall Time	t_f		-	10	-	
Drain-Source Body Diode Characteristics						
Maximum Body-Diode Continuous Current	I_s		-	-	5.6	A
Diode Forward Voltage	V_{SD}	$I_s=5.6\text{A}, V_{\text{GS}}=0\text{V}$	-	0.8	1.2	V

Notes: 1. Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.

2.Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

RATINGS AND CHARACTERISTIC OF JH3400A

Typical Performance Characteristics

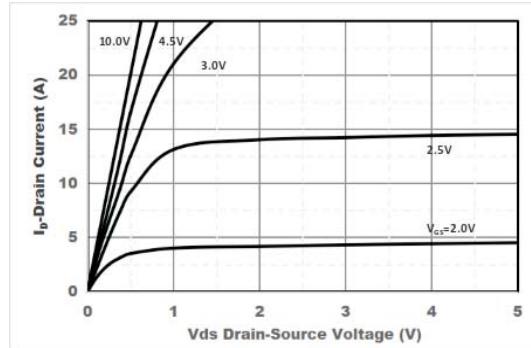


Figure1. Output Characteristics

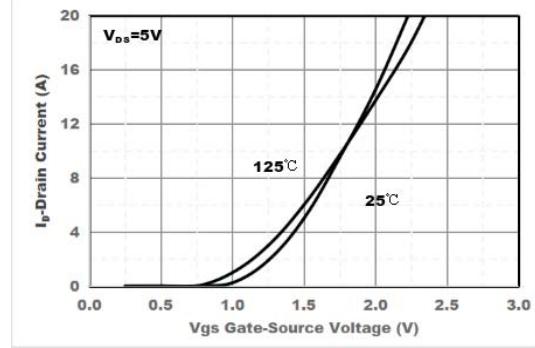


Figure2. Transfer Characteristics

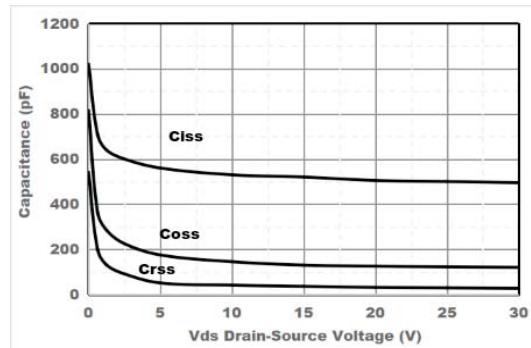


Figure3. Capacitance Characteristics

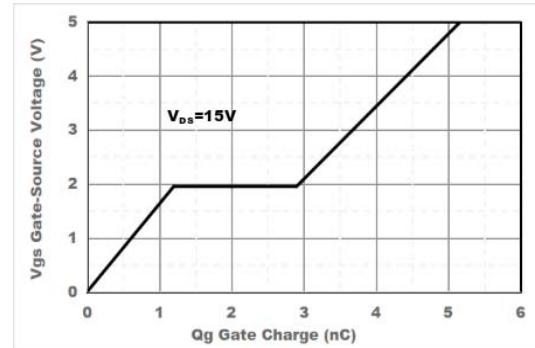


Figure4. Gate Charge

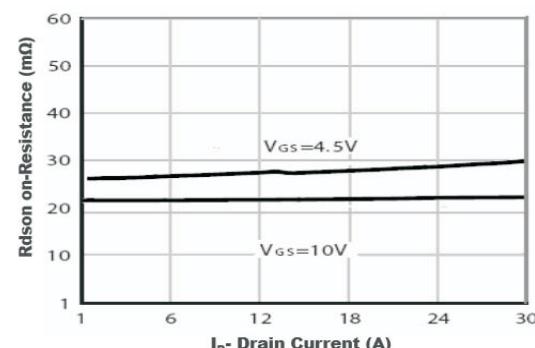


Figure5. Drain-Source on Resistance

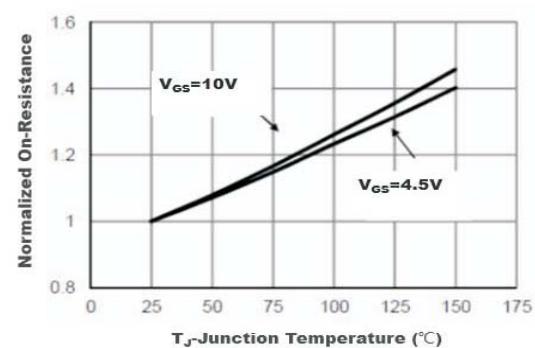


Figure6. Drain-Source on Resistance

RATINGS AND CHARACTERISTIC OF JH3400A

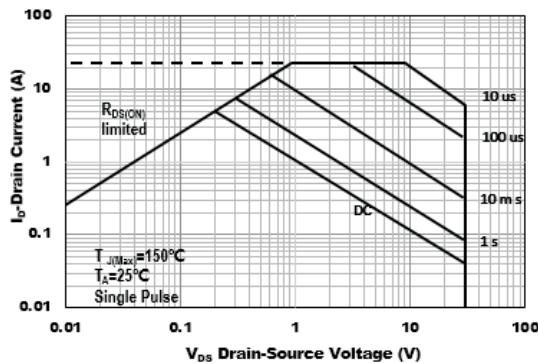


Figure7. Safe Operation Area

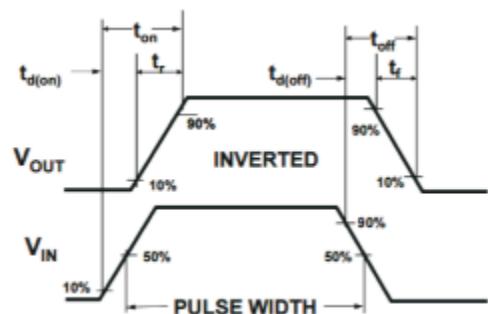
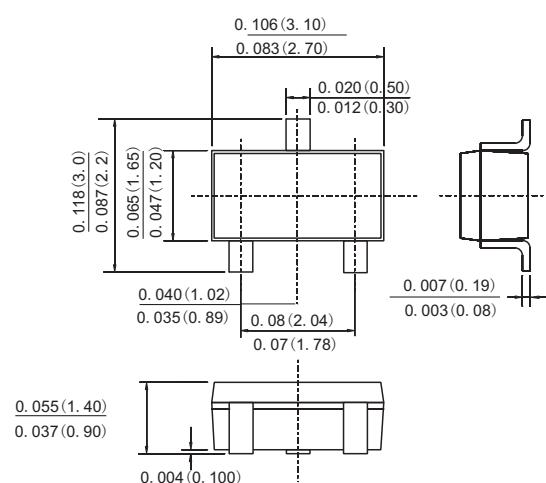


Figure8. Switching wave

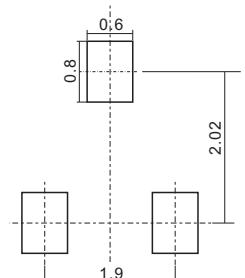
PACKAGE OUTLINE DIMENSIONS

SOT-23



Dimensions in inches and (millimeters)

Suggested Pad Layout



Dimensions in millimetres

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